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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/736,386	12/15/2003	Bruce Whitefield	03-1345	6227
24319	7590	03/05/2009		
LSI CORPORATION 1621 BARBER LANE MS: D-105 MILPITAS, CA 95035			EXAMINER JONES, HUGH M	
			ART UNIT 2128	PAPER NUMBER
			MAIL DATE 03/05/2009	DELIVERY MODE PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Office Action Summary

Application No.

10/736,386

Applicant(s)

WHITEFIELD ET AL.

Examiner

Hugh Jones

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 20 January 2009.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-21 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-21 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 15 December 2003 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☐ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO/5508)
- Paper No(s)/Mail Date _____

- 4) ☐ Interview Summary (PTO-413)
- Paper No(s)/Mail Date _____
- 5) ☐ Notice of Informal Patent Application
- 6) ☐ Other: _____

DETAILED ACTION

Introduction

1. Claims 1-21 of U.S. Application 10/736,386 filed 12/15/2003 are pending.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

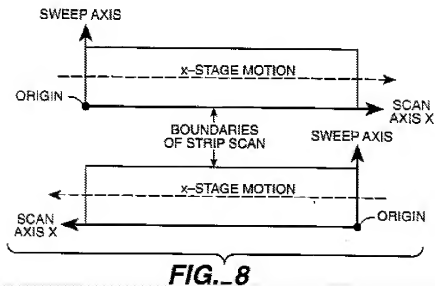
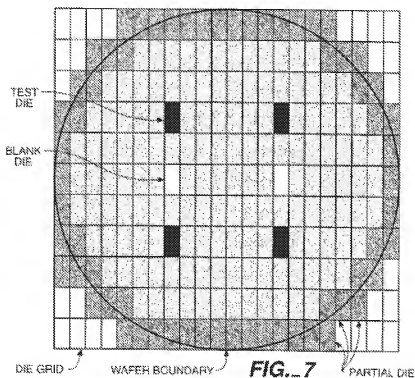
A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

3. Claims 1-2, 5-21 are rejected under 35 U.S.C. 102(b) as anticipated by Jordan III et al. (of record).
4. Jordan discloses a method for calculating high-resolution wafer parameter profiles comprising the steps of:
 - a. Defining an appropriate product/device input dataset (column 10 lines 35-46, data gathering and sampling on a surface) for a plurality of different die sizes and products (column 12 lines 51-64), wherein the dataset comprises physical correlation reference points comprising information relating to the size of each die in two directions as well as the location of at least one of the corners of each die; (See at least fig. 7-8).
 - b. Collecting a die level bin yield dataset for one of the products/devices defined in step (a) (column 12 lines 37-43) by using the product/device input dataset to generate a table of data for the lots and wafers of said one of the products/devices with the virtual

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die (column 12 lines 61-64) coordinate for each die and its corresponding value (sweeping, collecting a value for each value in the sweep, column 12 lines 44-51);



- c. Calculating a single composite value for each die coordinate (column 11 line 51-56, calculating intensity);
- d. Defining where on the virtual die it is desired to assign a composite value (column 12 line 65-column 13 line 2, intensity and aligning the beam with the virtual pattern on the location to be sampled);
- e. Calculating physical coordinates for each die value using the corresponding virtual coordinate and physical translation key (column 15 line 61-column 16 line 5, shows that coordinate locations are calculated for each intensity value);
- f. Repeating steps (b), (c), (d) and (e) for each of said die sizes and products defined in step (a) (column 14 lines 41-46, multiple events being processed);
- g. Merging the data from a plurality of files into one file (column 14 line 54, merging events);
- h. Defining a grid (column 10 lines 37-51);
- i. Creating a table with all the possible grid coordinates that would fit on a production wafer (column 25, line 47-column 26 line 6, generating convolution data given a wafer size);
- j. Defining a smoothing algorithm (column 16 lines 58-61, interpolation exploiting smooth shape);
- k. Calculating the smoothed value for each point on the grid from the combined data (column 16 lines 50-58); and
- l. Plotting a wafer profile (figures 18 and 19).

As per claim 2,

Jordan discloses normalizing the composite die values so that they are mergeable with values from the other products (column 11 lines 30-38, figure 1B, Gaussian distribution).

As per claim 5,

Jordan discloses the appropriate product/device input dataset being defined by a variety of devices sizes (column 12 lines 37-43, comparison of multiple strip units) with die level data and different die sizes (column 12 lines 52-61, different sizes of strip units).

As per claim 6,

Jordan discloses the appropriate product/device input dataset being defined by products/devices which represent the same process flow to be modeled (column 3 lines 54-64, finding intensities on all pixels).

As per claim 7,

Jordan discloses the appropriate product/device input dataset being defined by a sufficient number of lots from each device to calculate a reasonable average result value for each die (column 16 lines 36-39).

As per claim 8,

Jordan discloses the appropriate product/device input dataset being defined by die size for each device (column 12 lines 52-61).

As per claim 9,

Jordan discloses the appropriate product/device input dataset being defined by at least one reference physical correlation point between a specific virtual coordinate and an actual physical location on the wafer (column 12, line 65-column, 13 line 2).

As per claim 10,

Jordan discloses the calculated single composite value for each die coordinate being an average of the data from all the individual lots and wafers corresponding to the die site (column 20, lines 6-11).

As per claim 11,

Jordan discloses the calculated single composite value for each die coordinate being a max of the data from all the individual lots and wafers corresponding to the die site (column 20, lines 33-37).

As per claim 12,

Jordan discloses the calculated single composite value for each die coordinate being a sum of the data from all the individual lots and wafers corresponding to the die site (column 25 lines 47-56).

As per claim 13,

Jordan discloses the calculated single composite value for each die coordinate being a percentage of the data from all the individual lots and wafers corresponding die site (column 17 lines 38-45).

As per claim 14,

Jordan discloses the composite value being assigned to a corner of the die nearest an edge of the wafer (column 9 lines 29-31).

As per claim 15,

Jordan discloses the composite value being assigned to a corner of the die nearest a center of the wafer (column 10 lines 12-14).

As per claim 16,

Jordan discloses the composite value being assigned from a center of the die (column 17 lines 5-8).

As per claim 17,

Jordan discloses a Cartesian coordinate system being used to calculate physical coordinates (column 12 lines 20-23, stage coordinate).

As per claim 18,

Jordan discloses a polar coordinate system being used to calculate physical coordinates (column 12 lines 20-23, wafer coordinate).

As per claim 19,

Jordan discloses the wafer profile being scaled, in equal increments of a range of values (column 19 lines 38-44).

As per claim 20,

Jordan discloses the wafer profile being scaled in equal percentiles of the data (column 25 lines 6-11).

As per claim 21,

Jordan discloses the wafer profile being plotted to show a three-dimensional contour map of the data (figure 7).

Claim Rejections - 35 USC § 103

5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said

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subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

6. The factual inquiries set forth in *Graham v. John Deere Co.*, 383 U.S. 1, 148

USPQ 459 (1966), that are applied for establishing a background for determining

obviousness under 35 U.S.C. 103(a) are summarized as follows:

1. Determining the scope and contents of the prior art.
2. Ascertaining the differences between the prior art and the claims at issue.
3. Resolving the level of ordinary skill in the pertinent art.
4. Considering objective evidence present in the application indicating obviousness or nonobviousness.

7. Claim 3 is rejected under 35 U.S.C. 103(a) as being unpatentable over Jordan as applied to claims 1-2 and 5-21 above, in view of Mitsutake et al., US Patent no. 6,885,950.

8. Jordan does not disclose expressly a Poisson Defect Density normalizing algorithm being used to perform the step of normalizing the composite die values so that they are mergeable with values from the other products. Mitsutake discloses a method for extracting wafer parameters including using a Poisson Defect Density normalizing algorithm to normalize the data so that they can be merged (column 7 lines 14-23).

9. It would have been obvious, at the time of the present invention, to modify Jordan's wafer extraction method with Mitsutake's Poisson Defect Density normalizing algorithm in order to normalize composite die value so they can be merged with values from different products. The motivation for doing so would have been to represent random defects within the extracted wafer parameter profiles (Mitsutake column 7 lines

36-63).

10. Claim 4 is rejected under 35 U.S.C. 103(a) as being unpatentable over Jordan as applied to claims 1-2 and 5-21 above, in view of Maaya et al. US Patent no. 7,065,239.

11. Jordan does not disclose expressly a max-min scaling normalizing algorithm being used to perform the step of normalizing the composite die values so that they are mergeable with values from the other products. Maaya discloses a method for extracting wafer parameters including using a max-min scaling normalizing algorithm to normalize the data so that they can be merged (column 14 lines 32-42).

12. It would have been obvious, at the time of the present invention, to modify Jordan's wafer extraction method with Maaya 's max-min scaling normalizing algorithm in order to normalize composite die value so they can be merged with values from different products. The motivation for doing so would have been to stabilize the range of parameters for a wafer (Maaya column 14 lines 42-44).

Response to Arguments

13. Applicant's arguments filed 1/20/2009, have been fully considered and are not persuasive.

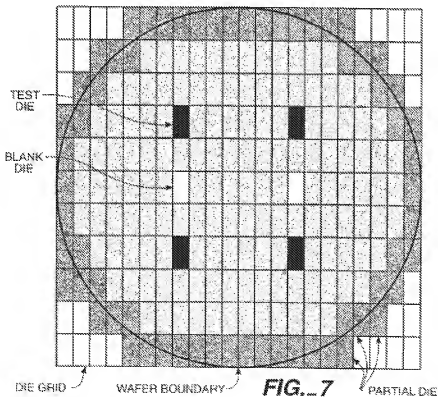
14. Applicants repeat the argument that (pg. 3):

Figure 7 of Jordan, III et al. merely illustrates a wafer, and the fact that it includes a repeating pattern (see col. 12, lines 37-43). Figure 7 of Jordan, III et al. discloses a plurality of dies on a wafer and that the dies have corners, etc., but does not disclose providing a dataset which comprises information relating to the size of each die in two directions as well as the location of at least one of the corners of each die.

15. Applicants also argue (pg. 3):

Applicant respectfully submits that Jordan, III et al. fails to disclose defining a dataset as recited in claim 1 (i.e., one which comprises physical correlation reference points comprising information relating to the size of each die in two directions as well as the location of at least one of the corners of each die), let alone using the dataset as recited in claim 1 (i.e., to generate a table of data for the lots and wafers of said one of the products/devices with a virtual die coordinate for each die and a corresponding value).

(Note the claim only requires "information relating to the size of each die in two dimensions as well as the location of at least one of the corners of each die"). See at least fig. 7 (cited in the rejection of the last office action for the same reasons):



The figure discloses at least a die grid including coordinates for the dies – in other words . *"information relating to the size of each die in two dimensions as well as the location of at least one of the corners of each die"*.

Conclusion

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire **THREE MONTHS** from the mailing date of this action. In the event a first reply is filed within **TWO MONTHS** of the mailing date of this final action and the advisory action is not mailed until after the end of the **THREE-MONTH** shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than **SIX MONTHS** from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to **Hugh Jones** whose telephone number is (571) 272-3781. The examiner can normally be reached on M-Th.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, **Kamini Shah** can be reached on (571) 272-2279. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Hugh Jones/
Primary Examiner, Art Unit 2128